NSN 5961-01-025-6193

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View Online at https://aerobasegroup.com/nsn/5961-01-025-6193 **Inclosure Material:** Metal **Overall Length:** Between 1.308 inches and 1.385 inches **Overall Height:** Between 0.660 inches and 0.798 inches Overall Width: 1.050 inches **End Application:** An/tpb-1c radar bomb dir set **Mounting Facility Quantity: Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: **Electrode Internally-electrically Connected To Case:** Collector **Mounting Method:** Unthreaded hole **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 700.0 breakdown voltage, collector-to-base, emitter open and 300.0 breakdown voltage, collector-to-emitter, base open and 5.0 breakdown voltage, emitter-to-base, collector open **Current Rating Per Characteristic:** 10.00 amperes zero-gate-voltage source current blank and 4.00 amperes zero-gate-voltage source current of standard range **Power Rating Per Characteristic:** 125.0 watts small-signal input power, common-collector preset **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** Junction pattern arrangement: npn **Terminal Type And Quantity:** 2 pin and 1 case Shelf Life: N/a **Unit Of Measure:**

No

Demilitarization:

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